

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

Complementary Silicon Plastic Power Transistor

DPAK-3 for Surface Mount Applications

Designed for low voltage, low-power, high-gain audio amplifier applications.

Features

- Collector-Emitter Sustaining Voltage –
 $V_{CE(sus)} = 100 \text{ Vdc (Min) @ } I_C$
 $= 10 \text{ mAdc}$
- High DC Current Gain –
 $h_{FE} = 40 \text{ (Min) @ } I_C$
 $= 200 \text{ mAdc}$
 $= 15 \text{ (Min) @ } I_C = 1.0 \text{ Adc}$
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Low Collector-Emitter Saturation Voltage –
 $V_{CE(sat)} = 0.3 \text{ Vdc (Max) @ } I_C$
 $= 500 \text{ mAdc}$
 $= 0.6 \text{ Vdc (Max) @ } I_C = 1.0 \text{ Adc}$
- High Current-Gain – Bandwidth Product –
 $f_T = 40 \text{ MHz (Min) @ } I_C$
 $= 100 \text{ mAdc}$
- Annular Construction for Low Leakage –
 $I_{CBO} = 100 \text{ nAdc @ Rated } V_{CB}$
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
 - Human Body Model, $3B > 8000 \text{ V}$
 - Machine Model, $C > 400 \text{ V}$
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Packages*



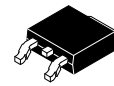
ON Semiconductor®

<http://onsemi.com>

**4.0 A, 100 V, 12.5 W
POWER TRANSISTOR**

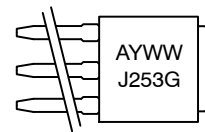


**IPAK
CASE 369D
STYLE 1**

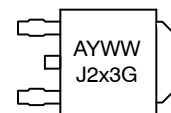


**DPAK-3
CASE 369C
STYLE 1**

MARKING DIAGRAMS



IPAK



DPAK

A = Assembly Location
 Y = Year
 WW = Work Week
 x = 4 or 5
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Base Voltage	V_{CB}	100	Vdc
Collector–Emitter Voltage	V_{CEO}	100	Vdc
Emitter–Base Voltage	V_{EB}	7.0	Vdc
Collector Current Continuous Peak	I_C	4.0 8.0	Adc
Base Current	I_B	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	12.5 0.1	W W/ $^\circ\text{C}$
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ (Note 2) Derate above 25°C	P_D	1.4 0.011	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted on minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction–to–Case Junction–to–Ambient (Note 2)	$R_{\theta JC}$ $R_{\theta JA}$	10 89.3	$^\circ\text{C/W}$

2. When surface mounted on minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	100	–	Vdc
Collector Cutoff Current ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$, $T_J = 125^\circ\text{C}$)	I_{CBO}	– –	100 100	nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 7.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	100	nAdc
DC Current Gain (Note 3) ($I_C = 200\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	40 15	180 –	–
Collector–Emitter Saturation Voltage (Note 3) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$) ($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$)	$V_{CE(sat)}$	– –	0.3 0.6	Vdc
Base–Emitter Saturation Voltage (Note 3) ($I_C = 2.0\text{ Adc}$, $I_B = 200\text{ mAdc}$)	$V_{BE(sat)}$	–	1.8	Vdc
Base–Emitter On Voltage (Note 3) ($I_C = 500\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.5	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 4) ($I_C = 100\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 10\text{ MHz}$)	f_T	40	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$)	C_{ob}	–	50	pF

3. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\approx 2\%$.

4. $f_T = |h_{FE}| \cdot f_{test}$.

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

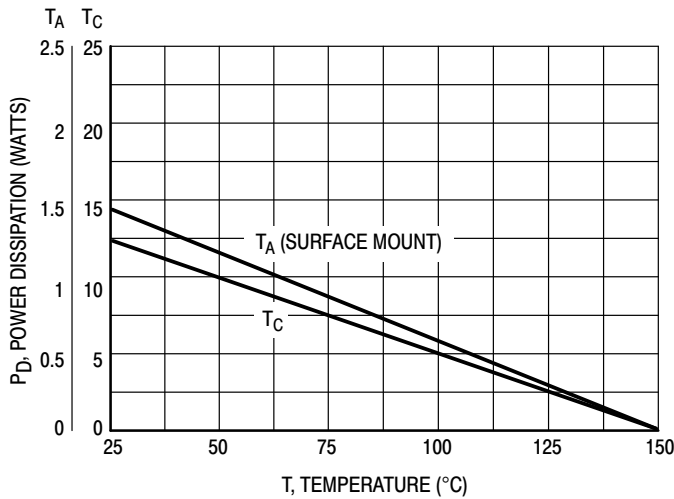


Figure 1. Power Derating

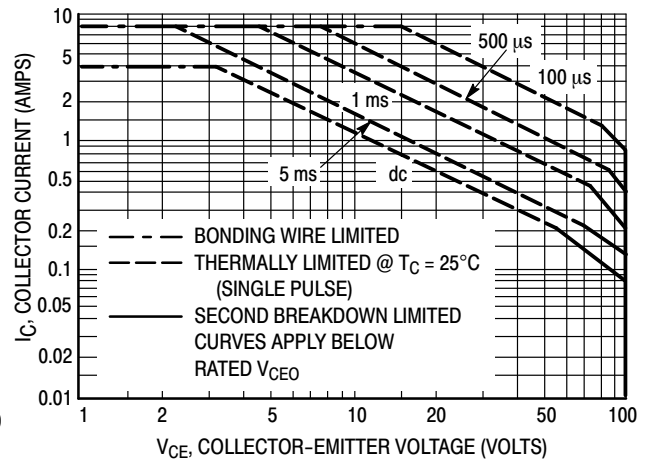


Figure 2. Active Region Maximum Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 3. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

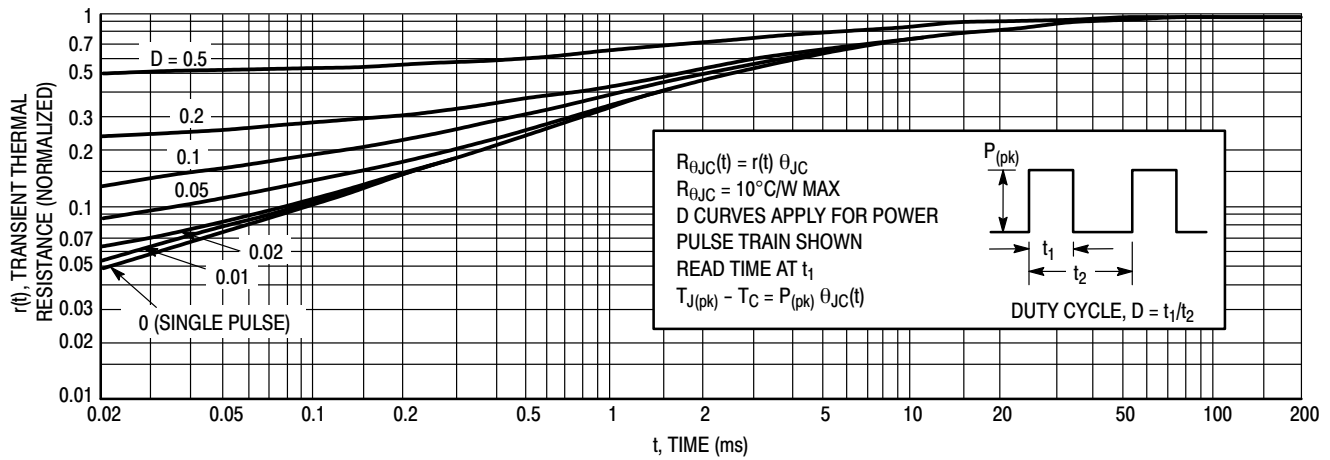
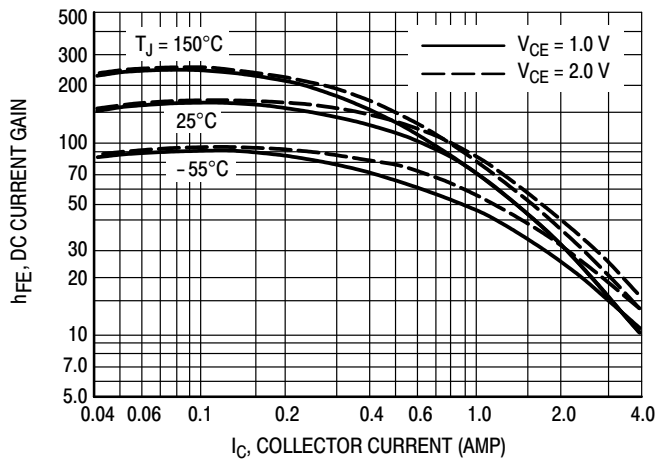


Figure 3. Thermal Response

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

**NPN
MJD243**



**PNP
MJD253**

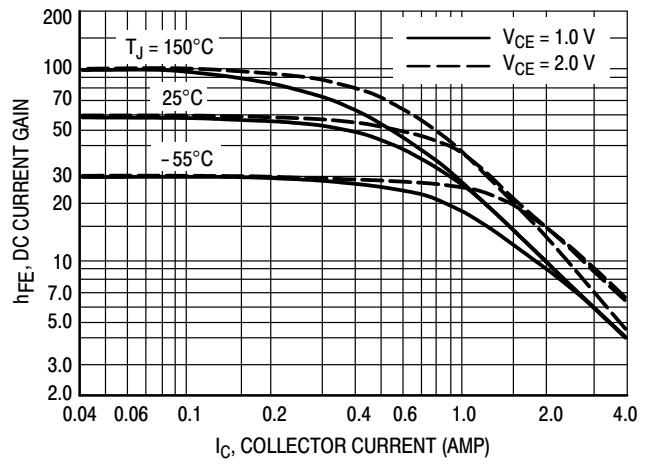


Figure 4. DC Current Gain

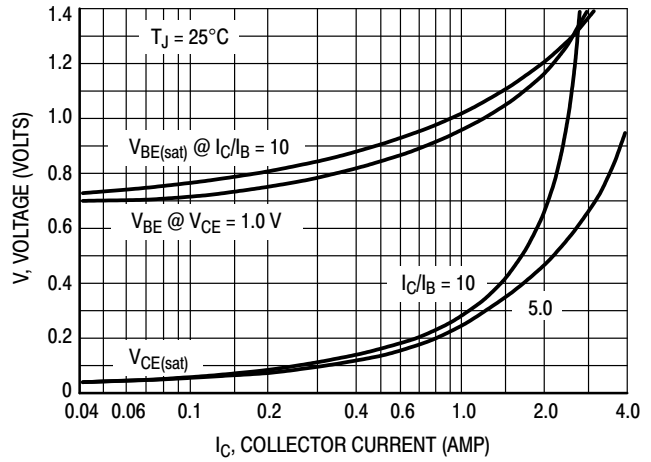
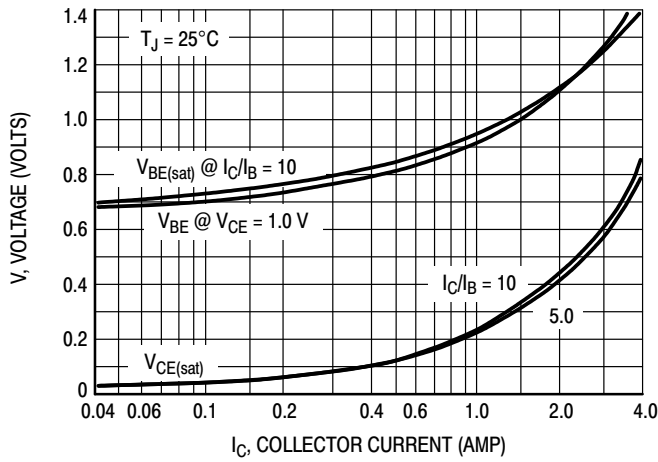


Figure 5. "On" Voltages

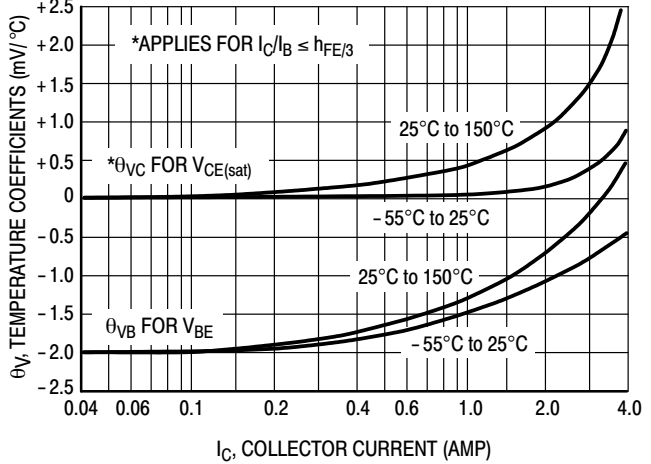
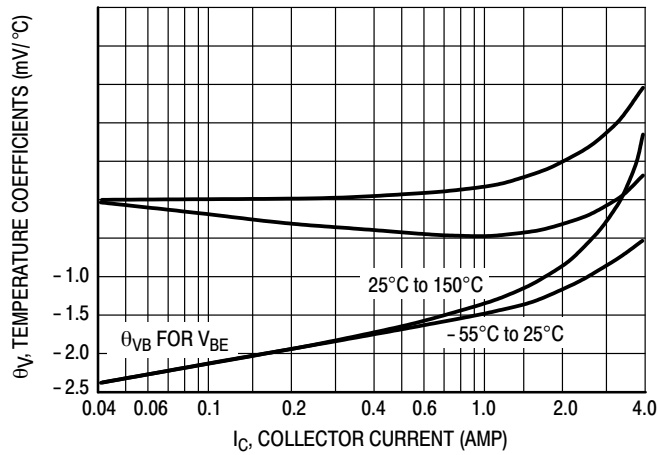


Figure 6. Temperature Coefficients

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

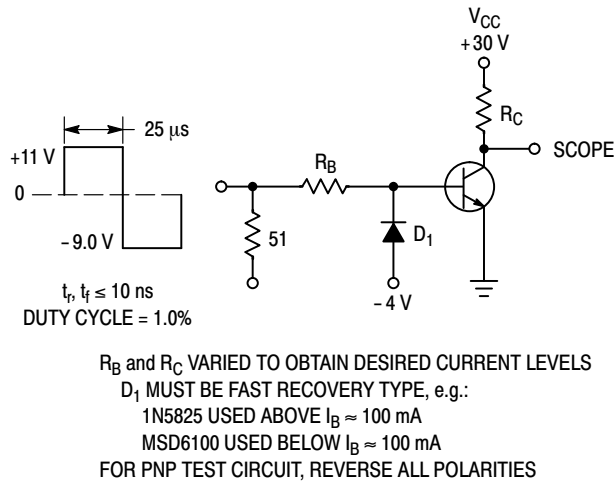


Figure 7. Switching Time Test Circuit

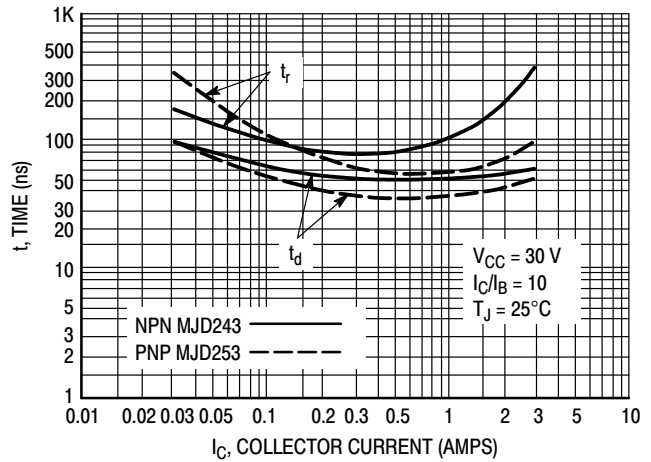


Figure 8. Turn-On Time

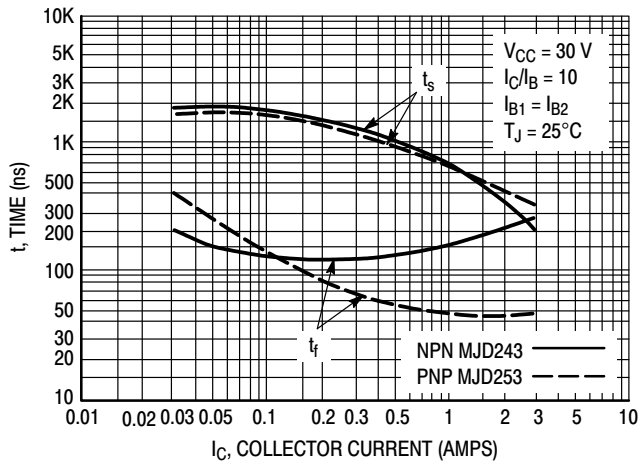


Figure 9. Turn-Off Time

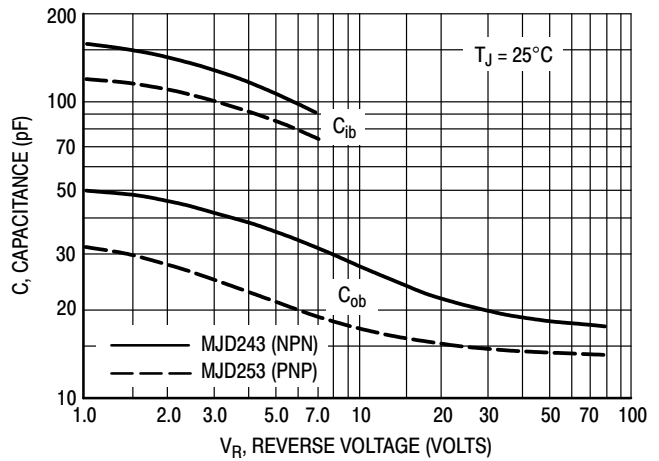


Figure 10. Capacitance

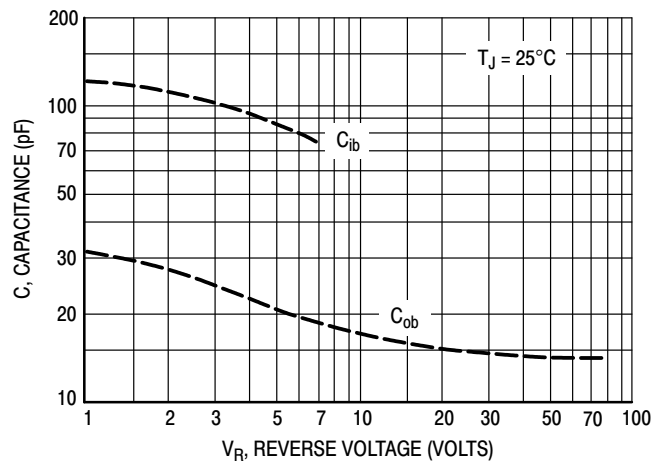


Figure 11. Capacitance

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

ORDERING INFORMATION

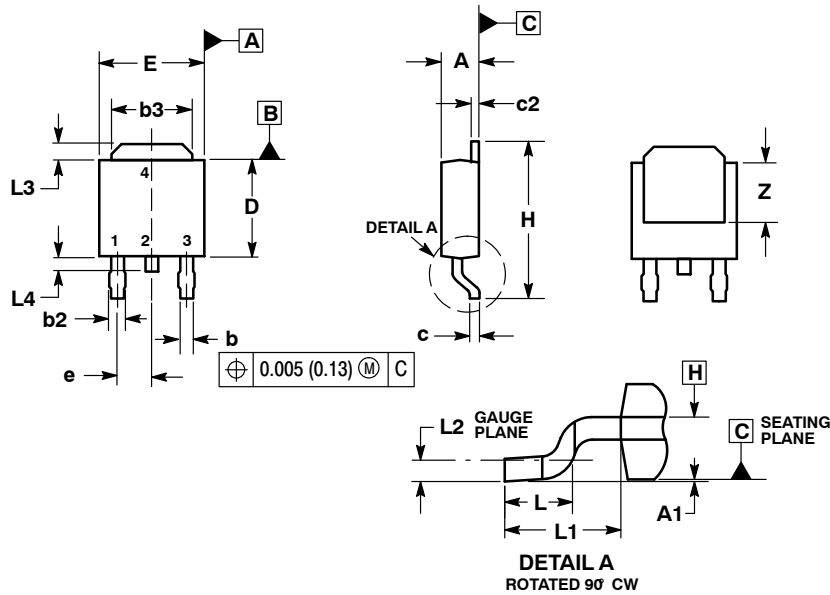
Device	Package Type	Package	Shipping [†]
MJD243G	DPAK-3 (Pb-Free)	369C	75 Units / Rail
MJD243T4G	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD243T4G	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel
MJD253-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD253T4G	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD253T4G	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

PACKAGE DIMENSIONS

DPAK-3 CASE 369C-01 ISSUE D

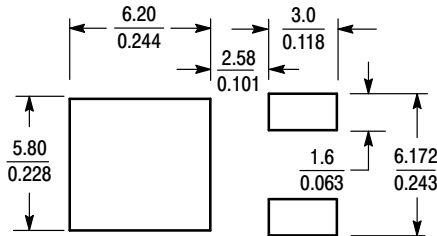


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	REF	2.74	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 (mm inches)

STYLE 1:

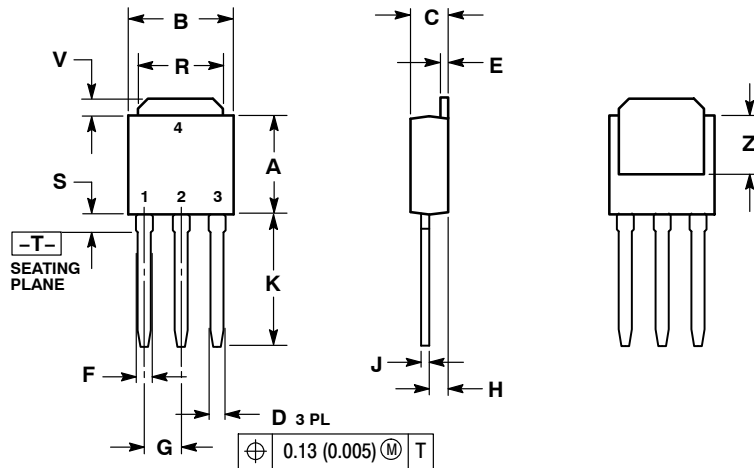
- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJD243, NJVMJD243T4G (NPN), MJD253, NJVMJD253T4G (PNP)

PACKAGE DIMENSIONS

IPAK CASE 369D-01 ISSUE C



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 1:
- PIN 1. BASE
 - 2. COLLECTOR
 - 3. EMITTER
 - 4. COLLECTOR

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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